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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

oplication of: Charm, Richard W. et al.

Confirmation No.: 6496

Application No.: 10/689,657

Group Art Unit: To be assigned

Filed: October 22, 2003

Examiner: To be assigned

For:

Process for the Use of Bis-Choline

and Tris-Choline in the Cleaning of

Quartz-Coated Polysilicon and Other

Materials

Attorney Docket No.: 60937-139-US

(formerly 8317-139-999)

TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above identified application.

<u>Please change the attorney docket number to 60937-139-US</u>. Future correspondence should be forwarded to James S. McDonald, customer no. **24341**.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310 (Order No. 60937-139-US). A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 12, 2004

James S. McDonald

(Reg. No. 44,229)

MORGAN, LEWIS & BOCKIUS LLP

3300 Hillview Avenue Palo Alto, CA 94304

(650) 493-4935



REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Date:

17 tob 2004

Signature:

Michael A Fury

Position/Title:

Typed Name:

Vice President, R&D and Engineering

Address:

2520 Barrington Court Hayward, CA 94545



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7 \ A. S.						
App #	. Title	⊹Inventor(s)	Filing Date		Former Attorney.	
	Compositions for Cleaning Organic					
	and Plasma Etched Residues for					
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999	
	Method of and Apparatus for					
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999	
	Chemical Mechanical Polishing					
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999	
	Oxalic Acid as a Semiaqueous					
10/404 706	Cleaning Product for Copper and	1	0.4/0.4/0.000			
10/421,706	Dielectrics Sulfoxide Pyrolid(in)one Alkanolamine	Lee, et al.	04/24/2003	60937-116-US	8317-116-999	
10/193,185	Cleaner Composition		07/49/2002	60007 440 140	0047 440 000	
10/193,103	Cleaner Composition	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999	
	Method for the Deposition of Materials		•			
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999	
	Post Etch Cleaning Composition for	vasquez, et al.	00/00/2001	00307-120-00	0317-120-999	
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999	
	Photolytic Conversion Process to					
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999	
	Cleaning Solutions Including					
	Nucleophilic Amine Compound			*		
	Having Reduction and Oxidation					
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999	
	Method and Compositions for					
10/000 100	Chemically Treating A Substrate	5	0.4.10.0.10.0.0			
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999	
	Cleaning Solution Including Nucleophilic Amine Compound					
	Having Reduction and Oxidation					
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-135-999	
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	60937-137-US	8317-133-999	
	Process for the Use of Bis-Choline	MONTH IN. OCHO	33/33/2003	00001-101-00	0311-131-888	
1	and Tris-Choline in the Cleaning of					
	Quartz-Coated Polysilicon and Other					
10/689,657	Materials	Charm, et al.	10/22/2003	60937-139-US	8317-139-999	
	Cleaning Compositions Containing	J. G. T. J. C. G.	10,22,2000	20007 100-00	2017-109-999	
	Hydroxylamine Derivatives and					
	Process Using Same for Residue					
10/689,620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999	

10/05	Composition for Exfoliation Agent to					
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999	
1	Reducing Oxide Loss When Using					
	Fluoride Chemistries to Remove Post-					
60/467,131	Etch Residues in Semiconductor	100 = 1=1	05/00/0000	60007 440 55	0047 440 000	
00/407,131	Processing	Lee, et al.	05/02/2003	60937-142-PR	8317-142-888	

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10/689,043 Polishing Composition and Polishing Process Containing Same Yao, et al. 10/21/2003 60937-151-US 8317-151-999 8317-171-999 8317-181-999 8317-18	60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
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10/257,469	10/280 270	1 -	Mukheriee et al	10/23/2002	60037-167-119	8317-167-000
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10/361,822 Enhance CMP Formulations Scott, et al. 02/11/2003 60937-179-US 8317-179-999 Titanium Carboxylate Films for Use in Semiconductor Processing Hill, et al. 02/26/2003 60937-182-US 8317-182-999 10/422,860 Method of Making Barrier Layers Maloney, et al. 05/20/2003 60937-183-US 8317-183-999 Remover Formulation Containing Fluoride for Use During Semiconductor Manufacturing Hirasawa, et al. 04/18/2003 60937-185-PR 8317-185-888 Cleaning Composition for Removing Resists and Manufacturing Method of Semiconductor Devices Hirasawa, et al. 04/21/2003 60937-186-PR 8317-186-888 Deposition of Permanent Polymer		_				
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Deposition of Permanent Polymer	60/464,125		Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
10/422,212 Structures for OLED Fabrication Roman, et al. 04/23/2003 60937-187-US 8317-187-999						
	10/422,212	Structures for OLED Fabrication	Roman, et al.	04/23/2003	60937-187-US	8317-187-999

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App #	Title	Inventor(s)		Docket No.	Docket No.
	Seimconductor Process Residue				
10/442,858	Removal Composition and Process	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
	Cleaning Compositions and Method of				1
10/630,300	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
	Compositions and Methods for				
	Rapidly Removing Overfilled				
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
	CMP Method for Copper, Tungsten,				
	Titanium, Polysilicon, and Other				
•	Substrates Using Organosulfonic				
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
	PeriodicAcid Compositions for				
	Polishing Nobel Metal/High K	5, ,,,	00/44/0000		
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
00/500 000	Cerium Oxide Abrasives for Chemical	Dahad Lonali	40/40/0000	00007 004 00	0047 004 000
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
	Chamical Machaniaal Polishing				
	Chemical Mechanical Polishing Slurries and Cleaners Containing			*	
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
00/310,730	Periodic Acid Compositions for	Carler, et al.	11/04/2003	00937-200-111	6517-200-666
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
00/494,933	Chemical Mechanical Polishing	Nobell 3. Siliali	00/14/2003	00937-207-17	0317-207-000
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
10/000,700	Alumia Abrasive for Chemical	Oman, or an	10/10/2000	00007 211 00	0017 211 000
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
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	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing				
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical				
	Mechanical Planarization of Tantalum				
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	60937-215-US	8317-215-999
	Alumina Abrasive for Chemical				
60/526,107	Mechanical Polishing	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
	Particulate or Particle-Bound				
60/509,922	Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
	Particulate or Particle-Bound				
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water	i			
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
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	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				
00/511 015	Dielectrics Using Superciritcal CO2	1	40/44/0000	00007.005.55	0047.005.055
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
10/604 000	Method and Apparatus for Substrate	1	10/00/0000	00027 000 110	0247 200 000
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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"App.#"#	Title	lñventor(s),	IFilling Date	New Attorney Docket No	Former Attorney
	Method of Chemically Mechanically				
60/515,450	Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888

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